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(54) **SEMICONDUCTOR DEVICE AND METHOD  
FOR MANUFACTURING THE SAME**

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**ABSTRACT**

A semiconductor device includes a substrate including at least one metal-oxide-semiconductor field-effect transistor (MOSFET) region defined by a device isolation layer and having an active pattern extending in a first direction on the MOSFET region, a gate electrode intersecting the active pattern on the substrate and extending in a second direction intersecting the first direction, and a first gate separation pattern adjacent to the MOSFET region when viewed from a plan view and dividing the gate electrode into segments spaced apart from each other in the second direction. The first gate separation pattern has a tensile strain when the MOSFET region is a P-channel MOSFET (PMOSFET) region. The first gate separation pattern has a compressive strain when the MOSFET region is an N-channel MOSFET (NMOSFET) region.

